

IN THE CLAIMS

Please amend the claims in accordance with the following rewritten claims in clean form. Applicant includes herewith an Attachment for Claim Amendments showing a marked up version of each amended claim.

Please cancel claims 19-29, without prejudice.

sub B1
A1

1. (Amended) A method for forming a bump comprising the steps of:
forming a resist layer so that a through-hole formed therein is located over
a pad; and
forming a metal post on the pad conforming to the shape of the through-hole,
wherein the metal post is formed so as to have a shape in which is formed
a recess for receiving a soldering or brazing material.

sub B2
A2

4. (Amended) The method for forming a bump according to claim 1,
wherein a plurality of the through-holes are formed in the resist layer so
that at least a part of each of the through-holes is superposed on the pad, and
a plurality of the metal posts are formed, each of the plurality of the metal
posts conforming to each of the through-holes to form the recess for receiving the
soldering or brazing material between the adjacent metal posts of the plurality of the
metal posts on the pad.

5. (Amended) The method for forming a bump according to claim 1,
wherein the metal post comprises first and second metal posts,
wherein the first metal post is formed in a state in which the resist layer is
formed, and the second metal post is formed on the first metal post.

A2
6. (Amended) A method for forming a bump comprising the steps of:
forming a resist layer so that a through-hole formed therein is located on a
pad; and
forming a metal layer to be electrically connected to the pad conforming to
the shape of the through-hole;
wherein the metal layer is formed so as to have a shape in which is
formed a region for receiving a soldering or brazing material;
wherein the metal layer comprises first and second metal layers,
wherein the first metal layer is formed in a state in which the resist layer is
formed, and
after removing the resist layer, the second metal layer is formed so as to
cover a surface of the first metal layer.

7. (Amended) The method for forming a bump according to claim 5,
wherein the pad is covered with an insulating film,
the resist layer is formed on the insulating film,
an opening for exposing at least part of the pad is formed in the insulating film
after forming the through-hole in the resist layer, and

A2

the first metal post is formed on the pad in a state in which the resist layer is formed.

A3
sub 5.7

9. (Amended) The method for forming a bump according to claim 5, wherein the first and second metal posts are formed by electroless plating.

A4
sub 5.7

11. (Amended) The method for forming a bump according to claim 5, wherein the first metal post is formed of a material containing nickel.

A5
sub 5.7

13. (Amended) The method for forming a bump according to claim 5, wherein the second metal post is formed of a material containing gold.

sub 5.7

15. (Amended) A method of fabricating a semiconductor device comprising the steps of:

A6

bonding a plurality of metal posts to a plurality of leads through a soldering or brazing material, each of the metal posts formed on each of a plurality of pads of a semiconductor chip, each of the metal posts having a shape in which is formed a recess for receiving the soldering or brazing material,

wherein the soldering or brazing material, when melted, is allowed to flow into the recess of each of the metal posts for receiving the soldering or brazing material so as not to spread onto an adjacent pad of the plurality of pads.

16. (Amended) The method of fabricating a semiconductor device according to claim 15,

wherein the recess is formed in a side of one of the metal posts, and the soldering or brazing material is allowed to flow into the recess.

17. (Amended) The method of fabricating a semiconductor device according to claim 15,

wherein one of the metal posts is formed so that the recess is formed in the direction of the height of the metal posts, and the soldering or brazing material is allowed to flow into the recess.

18. (Amended) The method of fabricating a semiconductor device according to claim 15,

wherein two or more metal posts of the plurality of metal posts are formed so as to be connected to one of the pads, and the soldering or brazing material is allowed to flow into a region formed between the adjacent metal posts of the plurality of metal posts on one of the pads.